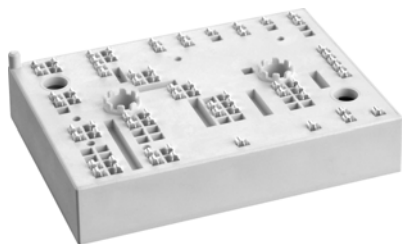


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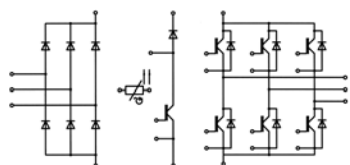
Features

- Trench 4 IGBT's
- Robust and soft freewheeling diodes in CAL technology
- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Remarks

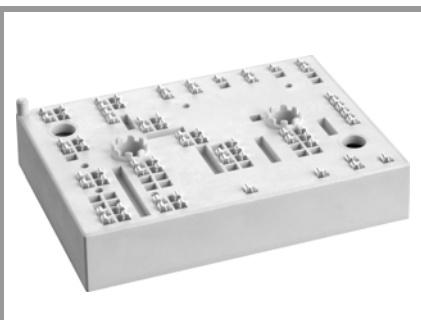
- V_{CEsat} , V_F = chip level value
- Case temp. limited to $T_C = 125^\circ\text{C}$ max. (for baseplateless modules $T_C = T_S$)
- product rel. results valid for $T_j \leq 150$ (recomm. Top = $-40 \dots +150^\circ\text{C}$)

Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
Inverter - IGBT				
V_{CES}	$T_j = 25^\circ\text{C}$		1200	V
I_C	$T_j = 150^\circ\text{C}$	$T_s = 25^\circ\text{C}$	47	A
		$T_s = 70^\circ\text{C}$	36	A
I_C	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	52	A
		$T_s = 70^\circ\text{C}$	43	A
I_{Cnom}			35	A
I_{CRM}	$I_{CRM} = 3 \times I_{Cnom}$		105	A
V_{GES}			-20 ... 20	V
t_{psc}	$V_{CC} = 800\text{ V}$ $V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 1200\text{ V}$	$T_j = 150^\circ\text{C}$	10	μs
T_j			-40 ... 175	$^\circ\text{C}$
Chopper - IGBT				
V_{CES}	$T_j = 25^\circ\text{C}$		1200	V
I_C	$T_j = 150^\circ\text{C}$	$T_s = 25^\circ\text{C}$	47	A
		$T_s = 70^\circ\text{C}$	36	A
I_C	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	52	A
		$T_s = 70^\circ\text{C}$	43	A
I_{Cnom}			35	A
I_{CRM}	$I_{CRM} = 3 \times I_{Cnom}$		105	A
V_{GES}			-20 ... 20	V
t_{psc}	$V_{CC} = 800\text{ V}$ $V_{GE} \leq 15\text{ V}$ $V_{CES} \leq 1200\text{ V}$	$T_j = 150^\circ\text{C}$	10	μs
T_j			-40 ... 175	$^\circ\text{C}$
Inverse - Diode				
V_{RRM}	$T_j = 25^\circ\text{C}$		1200	V
I_F	$T_j = 150^\circ\text{C}$	$T_s = 25^\circ\text{C}$	39	A
		$T_s = 70^\circ\text{C}$	30	A
I_F	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	44	A
		$T_s = 70^\circ\text{C}$	35	A
I_{Fnom}			35	A
I_{FRM}	$I_{FRM} = 3 \times I_{Fnom}$		105	A
I_{FSM}	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 150^\circ\text{C}$		170	A
T_j			-40 ... 175	$^\circ\text{C}$
Freewheeling - Diode				
V_{RRM}	$T_j = 25^\circ\text{C}$		1200	V
I_F	$T_j = 150^\circ\text{C}$	$T_s = 25^\circ\text{C}$	39	A
		$T_s = 70^\circ\text{C}$	30	A
I_F	$T_j = 175^\circ\text{C}$	$T_s = 25^\circ\text{C}$	44	A
		$T_s = 70^\circ\text{C}$	35	A
I_{Fnom}			35	A
I_{FRM}	$I_{FRM} = 3 \times I_{Fnom}$		105	A
I_{FSM}	$t_p = 10\text{ ms, sin } 180^\circ, T_j = 150^\circ\text{C}$		170	A
T_j			-40 ... 175	$^\circ\text{C}$



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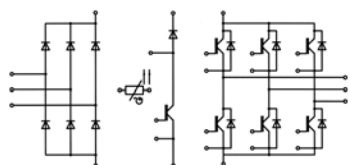
SKiIP 34NAB12T4V1

Features

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Remarks

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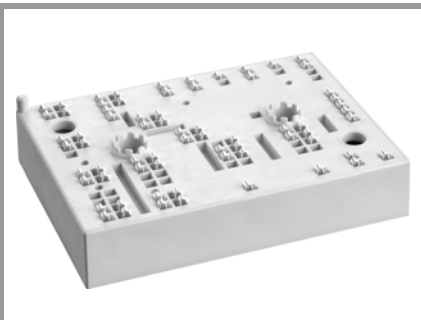


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Absolute Maximum Ratings			
Symbol	Conditions	Values	Unit
Rectifier - Diode			
V_{RRM}	$T_j = 25^\circ\text{C}$	1600	V
I_F	$T_s = 25^\circ\text{C}, T_j = 150^\circ\text{C}$	52	A
I_{Fnom}		13	A
I_{FSM}	10 ms	$T_j = 25^\circ\text{C}$	370
	sin 180°	$T_j = 150^\circ\text{C}$	270
I^2t	10 ms	$T_j = 25^\circ\text{C}$	685
	sin 180°	$T_j = 150^\circ\text{C}$	365
T_j		-40 ... 150	$^\circ\text{C}$
Module			
$I_{t(RMS)}$	$T_{terminal} = 80^\circ\text{C}, 20\text{A per spring}$	80	A
T_{stg}		-40 ... 125	$^\circ\text{C}$
V_{isol}	AC sinus 50Hz, 1 min	2500	V

Characteristics					
Symbol	Conditions	min.	typ.	max.	Unit
Inverter - IGBT					
$V_{CE(sat)}$	$I_C = 35\text{ A}$ $V_{GE} = 15\text{ V}$ chipllevel	$T_j = 25^\circ\text{C}$	1.85	2.10	V
		$T_j = 150^\circ\text{C}$	2.25	2.45	V
V_{CE0}		$T_j = 25^\circ\text{C}$	0.8	0.9	V
		$T_j = 150^\circ\text{C}$	0.7	0.8	V
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	30	34	m Ω
		$T_j = 150^\circ\text{C}$	44	47	m Ω
$V_{GE(th)}$	$V_{GE} = V_{CE}\text{ V}, I_C = 1\text{ mA}$	5	5.8	6.5	V
I_{CES}	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25^\circ\text{C}$	0.1	0.3	mA
					mA
C_{ies}	$V_{CE} = 25\text{ V}$ $V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	1.95		nF
C_{oes}		$f = 1\text{ MHz}$	0.16		nF
C_{res}		$f = 1\text{ MHz}$	0.12		nF
Q_G	- 8 V...+ 15 V		200		nC
R_{Gint}	$T_j = 25^\circ\text{C}$		0.00		Ω
$t_{d(on)}$	$V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$	30		ns
t_r	$I_C = 35\text{ A}$	$T_j = 150^\circ\text{C}$	35		ns
E_{on}	$R_{Gon} = 18\ \Omega$	$T_j = 150^\circ\text{C}$	4.3		mJ
$t_{d(off)}$	$R_{Goff} = 18\ \Omega$	$T_j = 150^\circ\text{C}$	300		ns
t_f		$T_j = 150^\circ\text{C}$	55		ns
E_{off}	$V_{GE} = +15/-15\text{ V}$	$T_j = 150^\circ\text{C}$	3.3		mJ
$R_{th(j-s)}$	per IGBT		0.85		K/W
Chopper - IGBT					
$V_{CE(sat)}$	$I_C = 35\text{ A}$ $V_{GE} = 15\text{ V}$ chipllevel	$T_j = 25^\circ\text{C}$	1.85	2.10	V
		$T_j = 150^\circ\text{C}$	2.25	2.45	V
V_{CE0}		$T_j = 25^\circ\text{C}$	0.8	0.9	V
		$T_j = 150^\circ\text{C}$	0.7	0.8	V
r_{CE}	$V_{GE} = 15\text{ V}$	$T_j = 25^\circ\text{C}$	30	34	m Ω
		$T_j = 150^\circ\text{C}$	44	47	m Ω
$V_{GE(th)}$	$V_{GE} = V_{CE}\text{ V}, I_C = 1\text{ mA}$	5	5.8	6.5	V
I_{CES}	$V_{GE} = 0\text{ V}$ $V_{CE} = 1200\text{ V}$	$T_j = 25^\circ\text{C}$	0.1	0.3	mA
		$T_j = 150^\circ\text{C}$			mA
Q_G	- 8 V...+ 15 V		200		nC
R_{Gint}	$T_j = 25^\circ\text{C}$		0.00		Ω

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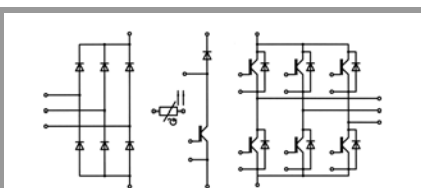
SKiIP 34NAB12T4V1

Features

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- Highly reliable spring contacts for electrical connections
- UL recognised file no. E63532

Remarks

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Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Chopper - IGBT						
$t_{d(on)}$	$V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$		30		ns
t_r	$I_C = 35\text{ A}$	$T_j = 150^\circ\text{C}$		35		ns
E_{on}	$R_{G\ on} = 18\ \Omega$	$T_j = 150^\circ\text{C}$		4.3		mJ
$t_{d(off)}$	$R_{G\ off} = 18\ \Omega$	$T_j = 150^\circ\text{C}$		300		ns
t_f		$T_j = 150^\circ\text{C}$		55		ns
E_{off}	$V_{GE} = +15/-15\text{ V}$	$T_j = 150^\circ\text{C}$		3.3		mJ
$R_{th(j-s)}$	per IGBT			0.85		K/W
Inverse - Diode						
$V_F = V_{EC}$	$I_F = 35\text{ A}$	$T_j = 25^\circ\text{C}$		2.3	2.6	V
	$V_{GE} = 0\text{ V}$ chiplevel	$T_j = 150^\circ\text{C}$		2.3	2.6	V
V_{F0}		$T_j = 25^\circ\text{C}$		1.3	1.5	V
		$T_j = 150^\circ\text{C}$		0.9	1.1	V
r_F		$T_j = 25^\circ\text{C}$		29	32	m Ω
		$T_j = 150^\circ\text{C}$		40	43	m Ω
I_{RRM}	$I_F = 35\text{ A}$	$T_j = 150^\circ\text{C}$		34		A
Q_{rr}	$di/dt_{off} = 1250\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		5.6		μC
E_{rr}	$V_{GE} = -15\text{ V}$ $V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$		2.4		mJ
$R_{th(j-s)}$	per Diode			1.2		K/W
Freewheeling - Diode						
$V_F = V_{EC}$	$I_F = 35\text{ A}$	$T_j = 25^\circ\text{C}$		2.3	2.6	V
	$V_{GE} = 0\text{ V}$ chiplevel	$T_j = 150^\circ\text{C}$		2.3	2.6	V
V_{F0}		$T_j = 25^\circ\text{C}$		1.3	1.5	V
		$T_j = 150^\circ\text{C}$		0.9	1.1	V
r_F		$T_j = 25^\circ\text{C}$		29	32	m Ω
		$T_j = 150^\circ\text{C}$		40	43	m Ω
I_{RRM}	$I_F = 35\text{ A}$	$T_j = 150^\circ\text{C}$		34		A
Q_{rr}	$di/dt_{off} = 1250\text{ A}/\mu\text{s}$	$T_j = 150^\circ\text{C}$		5.6		μC
E_{rr}	$V_{GE} = -15\text{ V}$ $V_{CC} = 600\text{ V}$	$T_j = 150^\circ\text{C}$		2.4		mJ
$R_{th(j-s)}$	per Diode			1.2		K/W
Rectifier - Diode						
$V_F = V_{EC}$	$I_F = 13\text{ A}$	$T_j = 25^\circ\text{C}$		1	1.21	V
	$V_{GE} = 0\text{ V}$ chiplevel	$T_j = 125^\circ\text{C}$			1.1	V
V_{F0}		$T_j = 25^\circ\text{C}$			1.0	V
		$T_j = 125^\circ\text{C}$			0.8	V
r_F		$T_j = 25^\circ\text{C}$		9.2	18	m Ω
		$T_j = 125^\circ\text{C}$			21	m Ω
$R_{th(j-s)}$	per Diode			1.25		K/W
Module						
M_s	to heat sink		2		2.5	Nm
w				95		g
Temperatur Sensor						
R_{100}	$T_r = 100^\circ\text{C}$, tolerance = 3 %			1670 \pm 3%		Ω
$R(T)$	$R(T) = 1000\ \Omega [1 + A(T - 25^\circ\text{C}) + B(T - 25^\circ\text{C})^2]$ $A = 7.635 \cdot 10^{-3}\ \text{C}^{-1}$, $B = 1.731 \cdot 10^{-5}\ \text{C}^{-2}$					

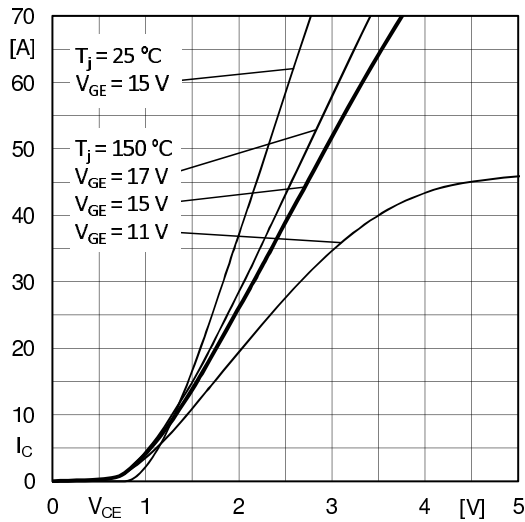


Fig. 1: Typ. output characteristic

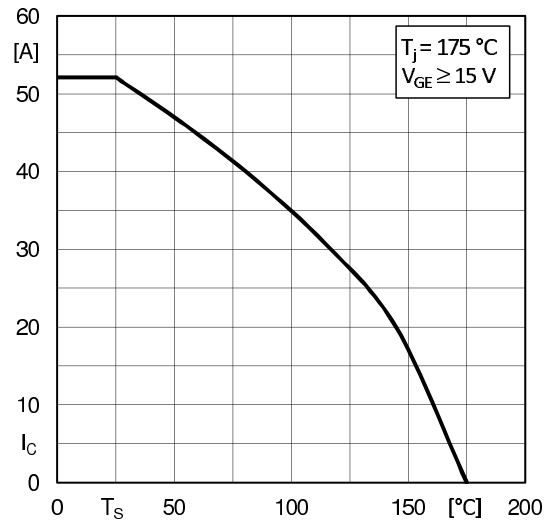


Fig. 2: Typ. rated current vs. temperature $I_C = f(T_S)$

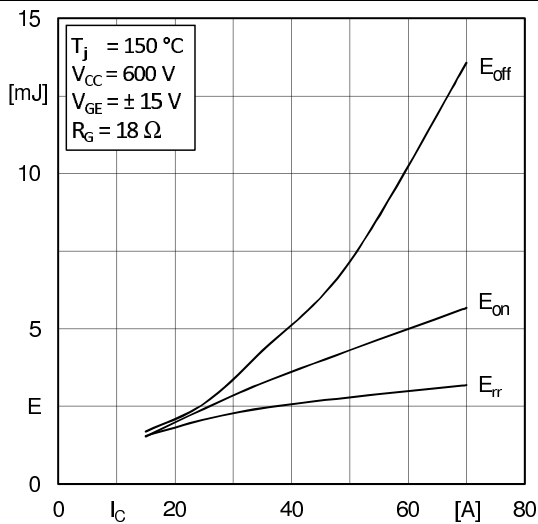


Fig. 3: Typ. turn-on /-off energy = f(Ic)

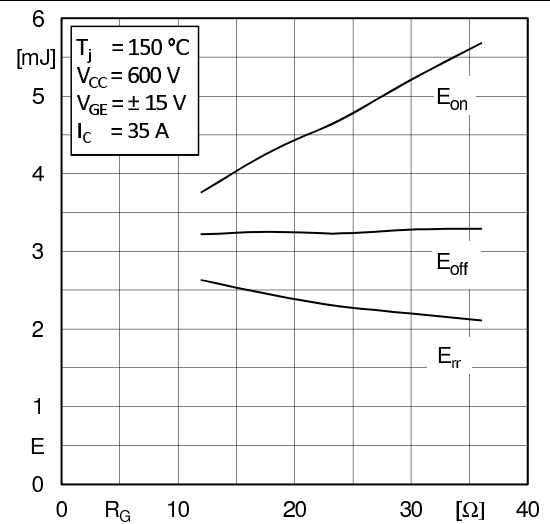


Fig. 4: Typ. turn-on /-off energy = f(Rg)

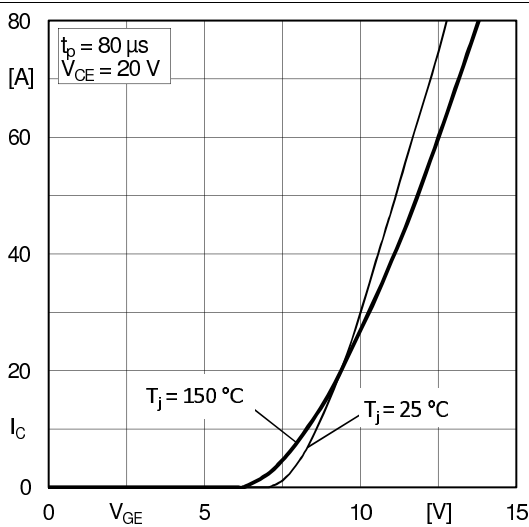


Fig. 5: Typ. transfer characteristic

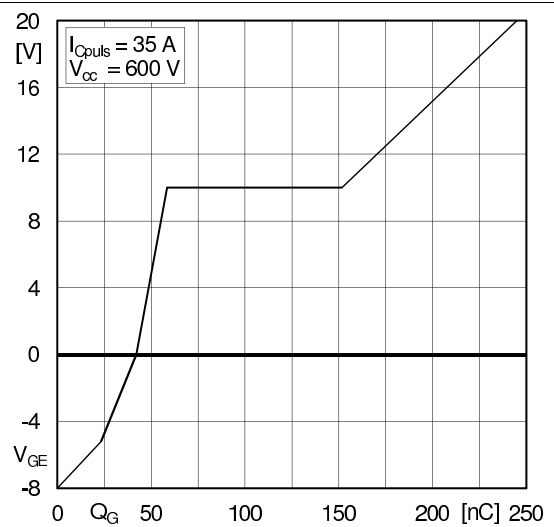


Fig. 6: Typ. gate charge characteristic

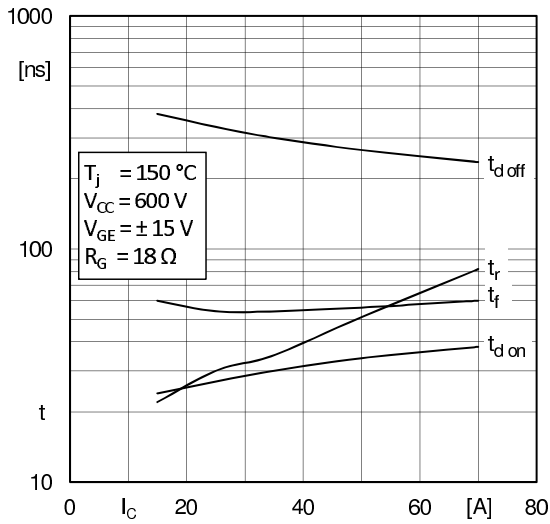


Fig. 7: Typ. switching times vs. I_C

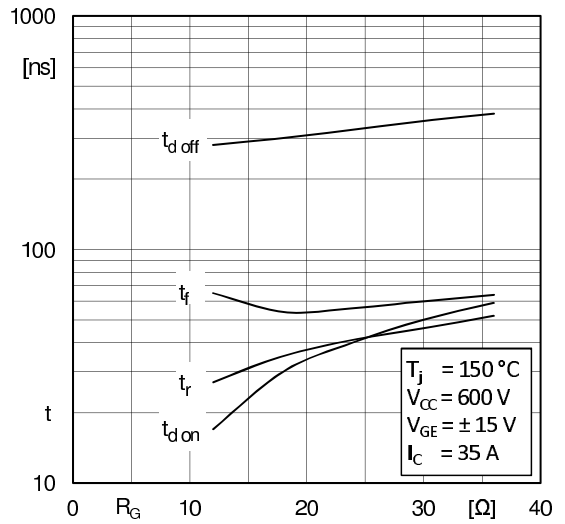


Fig. 8: Typ. switching times vs. gate resistor R_G

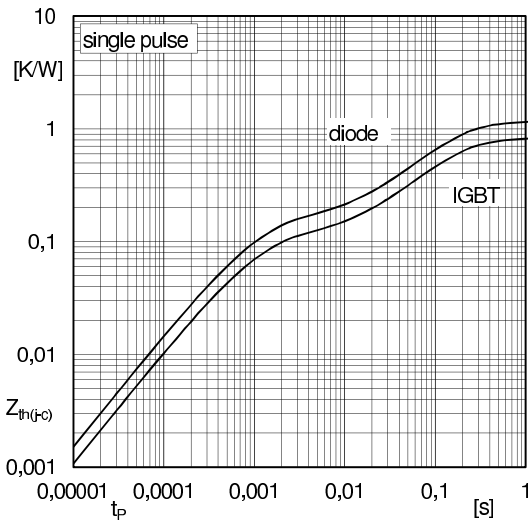


Fig. 9: Transient thermal impedance of IGBT and Diode

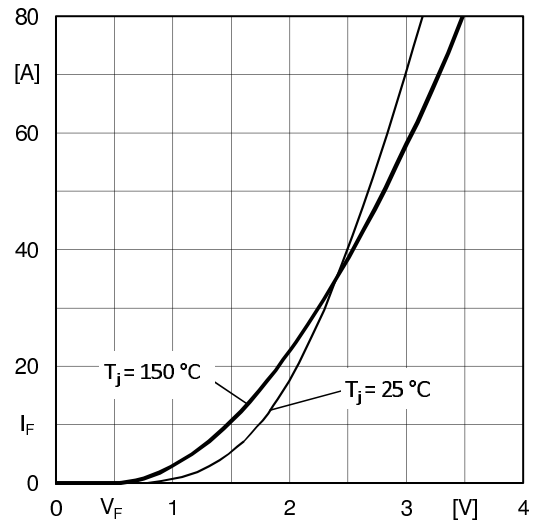


Fig. 10: CAL diode forward characteristic

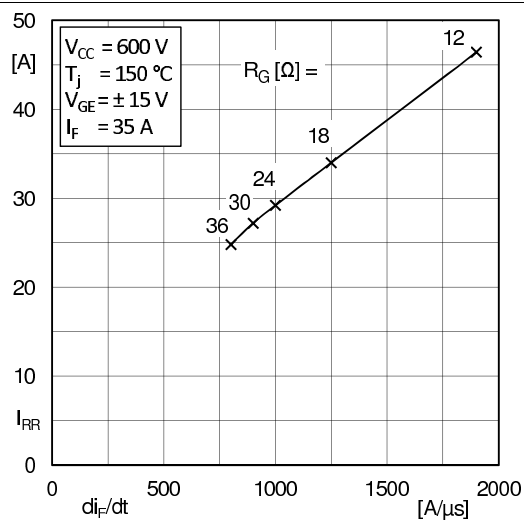


Fig. 11: Typ. CAL diode peak reverse recovery current

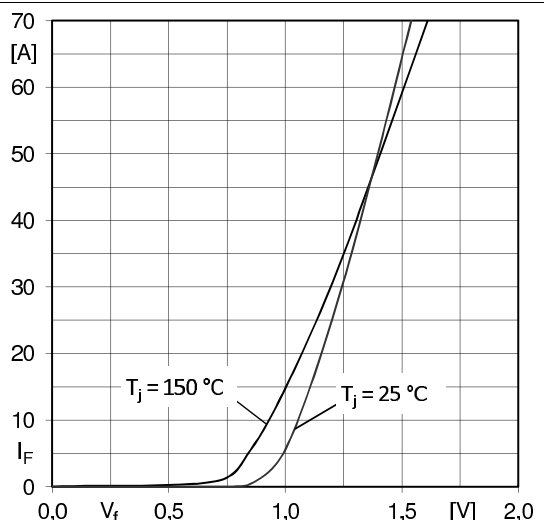
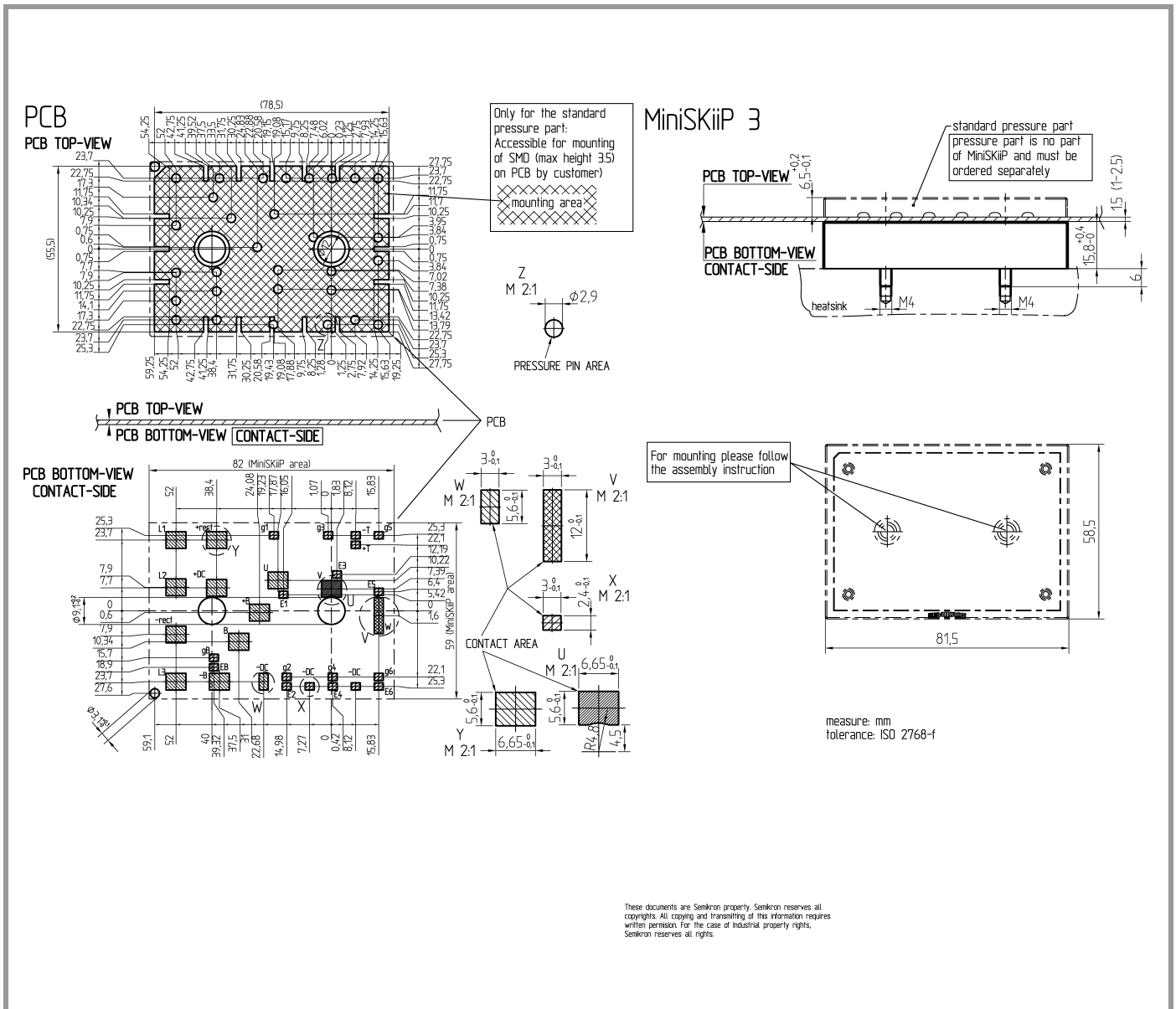
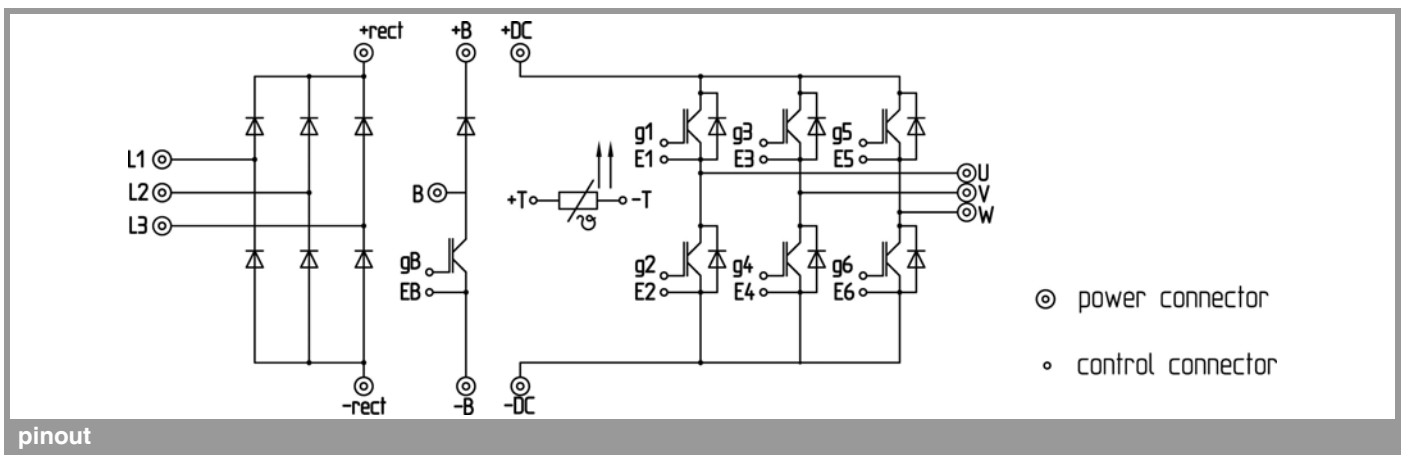


Fig. 12: Typ. input bridge forward characteristic

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pinout, dimensions



pinout

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.